RS1AF THRU RS1MF

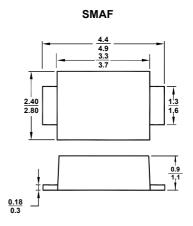
Surface Mount Fast Recovery Rectifier Reverse Voltage - 50 to 1000 V Forward Current - 1 A

Features

- Glass Passivated Chip Juntion
- For surface mounted applications
- Low profile package
- Fast reverse recovery time

Mechanical Data

- Case: SMAF
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026



All Dimensions in mm

Absolute Maximum Ratings and Characteristics

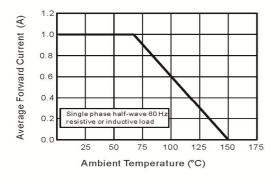
Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

V									
Deremeter	Symbols	RS1AF	RS1BF	RS1DF	RS1GF	RS1JF	RS1KF	RS1MF	Units
Parameter		RS1A	RS1B	RS1D	RS1G	RS1J	RS1K	RS1M	-
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _a = 65°C	I _{F(AV)}	1							А
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	30						А	
Maximum Forward Voltage at 1 A	VF	1.3						V	
Maximum Reverse Current $T_a = 25^{\circ}C$ at Rated DC Blocking Voltage $T_a = 125^{\circ}C$	I _R	5 50							μA
Typical Junction Capacitance at $V_R = 4 V$, f = 1 MHZ	Cj	15						pF	
Typical Thermal Resistance ¹⁾	$R_{ extsf{ heta}JA}$	115						°C/W	
Maximum Reverse Recovery Time at $I_F = 0.5 A$, $I_R = 1 A$, $I_{rr} = 0.25 A$	t _{rr}		1	50		250	50	00	ns
Operating Junction and Storage Temperature Range	Tj, T _{stg}	- 55 to + 150							°C

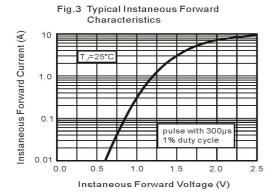
1) P.C.B. mounted with 0.2 X 0.2" (5 X 5 mm) copper pad areas.



TOP DYNAMIC







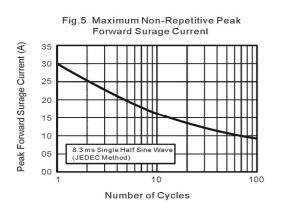


Fig.2 Typical Reverse Characteristics

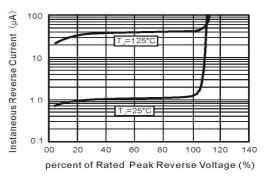
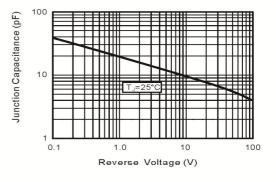


Fig.4 Typical Junction Capacitance





TOP DYNAMIC